

PRELIMINARY

PM50RLA120

FLAT-BASE TYPE
INSULATED PACKAGE

Notice : This is not a final specification. Some parametric limits are subject to change.

PM 50RLA120

Pre.	<i>T. Moriwaka</i>	Rev.	
Apr.	<i>m. Yamamoto</i> <i>Sep 30 '92</i>		

Feature

- a) Adopting new 5th generation IGBT(CSTBT) chip, which performance is improved by 1 μ m fine rule process.
For example, typical $V_{ce(sat)}=1.9V$ @ $T_j=125^{\circ}C$
 - b) I adopt the over-temperature conservation by T_j detection of CSTBT chip, and error output is possible from all each conservation upper and lower arm of IPM.
 - c) New small package
Reduce the package size by 10%, thickness by 22% from S-DASH series.
 - d) Current rating of brake part increased.
50% for the current rating of inverter part.
- 3 ϕ 50A,1200V Current-sense IGBT type inverter
 - 25A,1200V Current-sense regenerative brake IGBT
 - Monolithic gate drive & protection logic
 - Detection, protection & status indication circuits for, short-circuit, over-temperature & under-voltage (P-Fo available from upper arm devices)
 - Acoustic noise-less 5.5kW/7.5kW class inverter application

OUTLINE DRAWING Dimensions in mm

See Page 7

APPLICATION : General purpose inverter, servo drives and other motor controls

